

Pb Free Plating Product

DK48N80



N-Channel Trench Process Power MOSFET Transistors

General Description

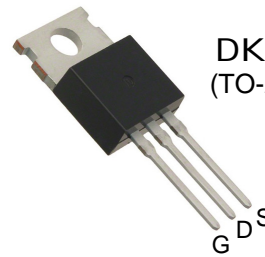
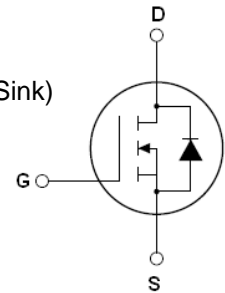
The DK48N80 is N-channel MOS Field Effect Transistor designed for high current switching applications. Rugged EAS capability and ultra low $R_{DS(ON)}$ is suitable for PWM, load switching especially for E-Bike controller applications.

Features

- $V_{DS}=70V$; $I_D=80A@V_{GS}=10V$;
 $R_{DS(ON)}<5.8m\Omega @V_{GS}=10V$
- Special Designed for E-Bike Controller Application
- Ultra Low On-Resistance
- High UIS and UIS 100% Test

Application

- 48V E-Bike Controller Applications
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

DK48N80
(TO-220 HeatSink)

Schematic Diagram

$$V_{DSS} = 70V$$

$$I_{DSS} = 80A$$

$$R_{DS(ON)} = 5.5m\Omega$$

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	70	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 25	V
$I_{D(DC)}$	Drain Current (DC) at $T_c=25^\circ C$	80	A
$I_{D(DC)}$	Drain Current (DC) at $T_c=100^\circ C$	78	A
$I_{DM(pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	320	A
dv/dt	Peak Diode Recovery Voltage	30	V/ns
P_D	Maximum Power Dissipation($T_c=25^\circ C$)	145	W
	Derating Factor	1.9	W/°C
E_{AS}	Single Pulse Avalanche Energy (Note 2)	590	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.EAS condition: $T_J=25^\circ C, V_{DD}=33V, V_G=10V, I_D=48.5A$

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	$^{\circ}C/W$

Table 3. Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$		70		V
I_{DSS}	Zero Gate Voltage Drain Current($T_c=25^{\circ}C$)	$V_{DS}=68V, V_{GS}=0V$			1	μA
I_{DSS}	Zero Gate Voltage Drain Current($T_c=125^{\circ}C$)	$V_{DS}=68V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=40A$		5.5	5.8	m Ω
Dynamic Characteristics						
g_{FS}	Forward Transconductance	$V_{DS}=10V, I_D=40A$		28		S
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$		3200		pF
C_{oss}	Output Capacitance			350		pF
C_{rss}	Reverse Transfer Capacitance			320		pF
Q_g	Total Gate Charge		$V_{DS}=30V, I_D=30A,$ $V_{GS}=10V$		75	
Q_{gs}	Gate-Source Charge			14		nC
Q_{gd}	Gate-Drain Charge			20		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$		12		nS
t_r	Turn-on Rise Time			14		nS
$t_{d(off)}$	Turn-Off Delay Time			25		nS
t_f	Turn-Off Fall Time			30		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)			80		A
I_{SDM}	Pulsed Source-Drain Current(Body Diode)			320		A
V_{SD}	Forward on Voltage (Note 1)	$T_J=25^{\circ}C, I_{SD}=40A, V_{GS}=0V$		0.8	0.95	V
t_{rr}	Reverse Recovery Time (Note 1)	$T_J=25^{\circ}C, I_F=75A$ $di/dt=100A/\mu s$		45		nS
Q_{rr}	Reverse Recovery Charge (Note 1)			90		nC
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

Notes 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$